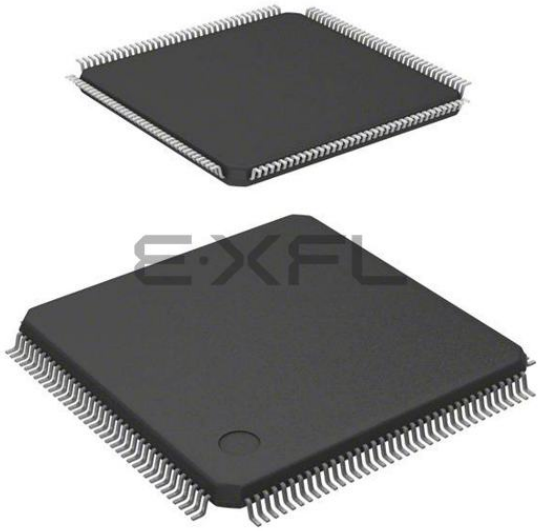

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"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M3
Core Size	32-Bit Single-Core
Speed	32MHz
Connectivity	I²C, IrDA, LINbus, SPI, UART/USART, USB
Peripherals	Brown-out Detect/Reset, Cap Sense, DMA, I²S, LCD, POR, PWM, WDT
Number of I/O	115
Program Memory Size	512KB (512K x 8)
Program Memory Type	FLASH
EEPROM Size	16K x 8
RAM Size	80K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 3.6V
Data Converters	A/D 40x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	144-LQFP
Supplier Device Package	144-LQFP (20x20)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32l152zet6

Contents

2 Description

The ultra-low-power STM32L151xE and STM32L152xE devices incorporate the connectivity power of the universal serial bus (USB) with the high-performance ARM® Cortex®-M3 32-bit RISC core operating at a frequency of 32 MHz (33.3 DMIPS), a memory protection unit (MPU), high-speed embedded memories (Flash memory up to 512 Kbytes and RAM up to 80 Kbytes), and an extensive range of enhanced I/Os and peripherals connected to two APB buses.

The STM32L151xE and STM32L152xE devices offer two operational amplifiers, one 12-bit ADC, two DACs, two ultra-low-power comparators, one general-purpose 32-bit timer, six general-purpose 16-bit timers and two basic timers, which can be used as time bases.

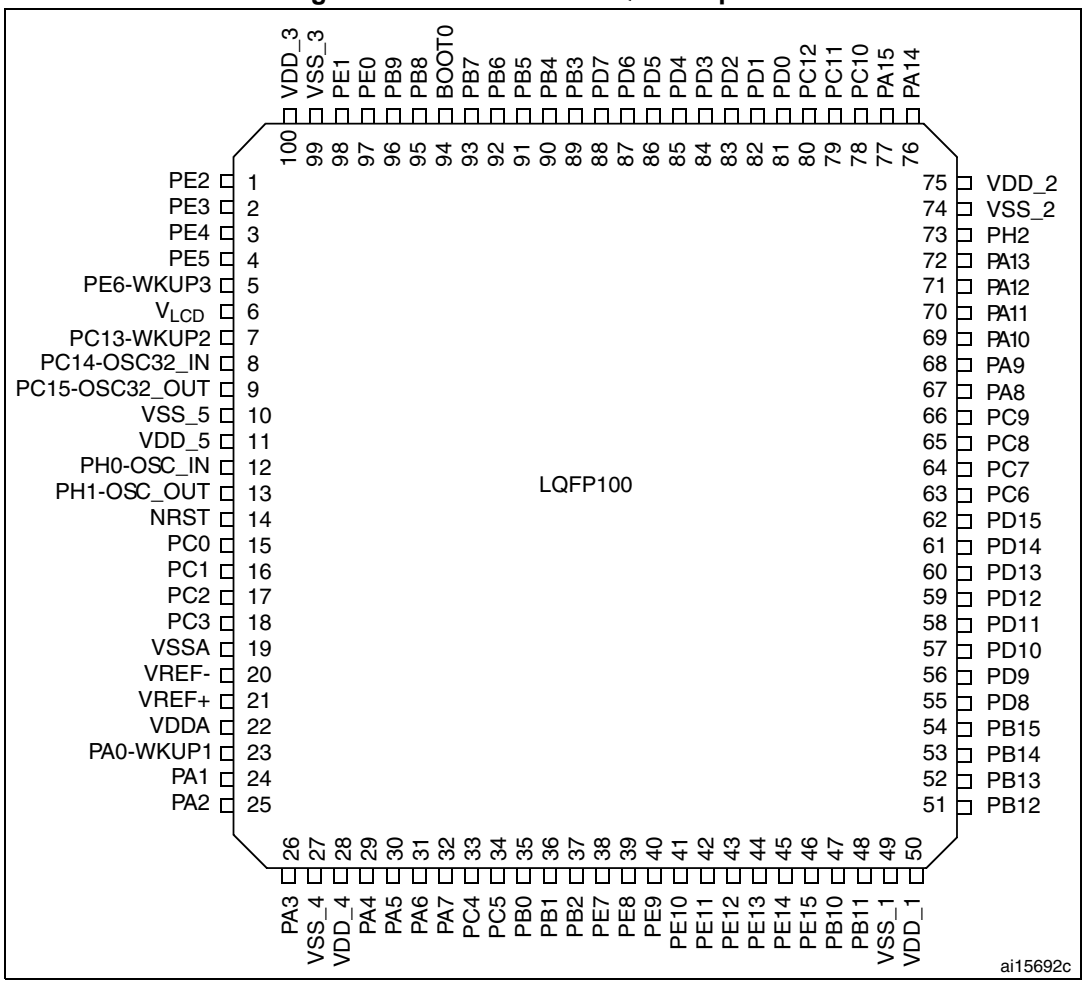
Moreover, the STM32L151xE and STM32L152xE devices contain standard and advanced communication interfaces: up to two I2Cs, three SPIs, two I2S, three USARTs, two UARTs and an USB. The STM32L151xE and STM32L152xE devices offer up to 34 capacitive sensing channels to simply add a touch sensing functionality to any application.

They also include a real-time clock and a set of backup registers that remain powered in Standby mode.

Finally, the integrated LCD controller (except STM32L151xE devices) has a built-in LCD voltage generator that allows to drive up to 8 multiplexed LCDs with the contrast independent of the supply voltage.

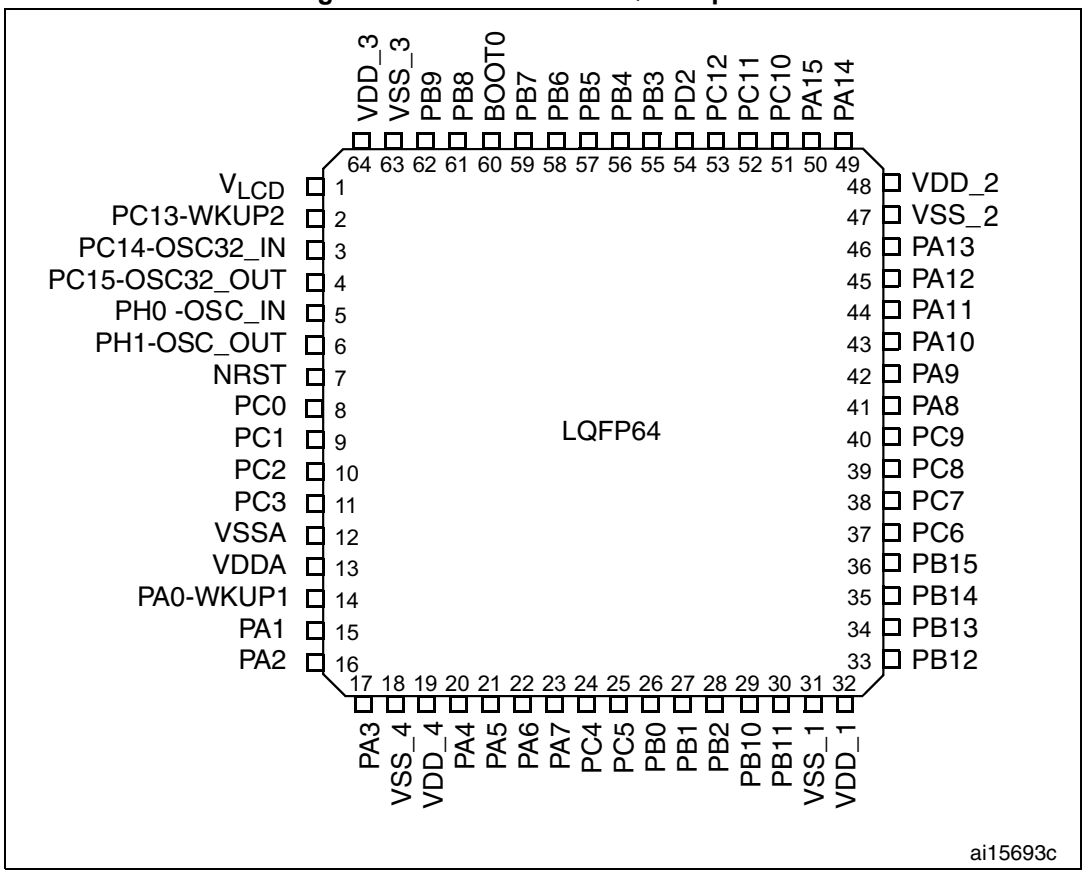
The ultra-low-power STM32L151xE and STM32L152xE devices operate from a 1.8 to 3.6 V power supply (down to 1.65 V at power down) with BOR and from a 1.65 to 3.6 V power supply without BOR option. They are available in the -40 to +85 °C and -40 to +105 °C temperature ranges. A comprehensive set of power-saving modes allows the design of low-power applications.

Figure 5. STM32L15xVE LQFP100 pinout



1. This figure shows the package top view.

Figure 6. STM32L15xRE LQFP64 pinout



1. This figure shows the package top view.

Table 8. STM32L151xE and STM32L152xE pin definitions (continued)

Pins					Pin name	Pin Type(1)	I / O structure	Main function(2) (after reset)	Pin functions	
LQFP144	UFBGA132	LQFP100	LQFP64	WLCSP104					Alternate functions	Additional functions
79	J12	57	-	K1	PD10	I/O	FT	PD10	USART3_CK/ LCD_SEG30	-
80	J11	58	-	G4	PD11	I/O	FT	PD11	USART3_CTS/ LCD_SEG31	-
81	J10	59	-	H3	PD12	I/O	FT	PD12	TIM4_CH1/ USART3_RTS/ LCD_SEG32	-
82	H12	60	-	H2	PD13	I/O	FT	PD13	TIM4_CH2/LCD_SEG33	-
83	-	-	-	-	V_{SS_8}	S	-	V_{SS_8}	-	-
84	-	-	-	-	V_{DD_8}	S	-	V_{DD_8}	-	-
85	H11	61	-	J1	PD14	I/O	FT	PD14	TIM4_CH3/LCD_SEG34	-
86	H10	62	-	G3	PD15	I/O	FT	PD15	TIM4_CH4/LCD_SEG35	-
87	G10	-	-	-	PG2	I/O	FT	PG2	-	ADC_IN10b
88	F9	-	-	-	PG3	I/O	FT	PG3	-	ADC_IN11b
89	F10	-	-	-	PG4	I/O	FT	PG4	-	ADC_IN12b
90	E9	-	-	-	PG5	I/O	FT	PG5	-	-
91	-	-	-	-	PG6	I/O	FT	PG6	-	-
92	-	-	-	-	PG7	I/O	FT	PG7	-	-
93	-	-	-	-	PG8	I/O	FT	PG8	-	-
94	F6	-	-	-	V_{SS_9}	S	-	V_{SS_9}	-	-
95	G6	-	-	-	V_{DD_9}	S	-	V_{DD_9}	-	-
96	E12	63	37	H1	PC6	I/O	FT	PC6	TIM3_CH1/I2S2_MCK/ LCD_SEG24	-
97	E11	64	38	G1	PC7	I/O	FT	PC7	TIM3_CH2/I2S3_MCK/ LCD_SEG25	-
98	E10	65	39	G2	PC8	I/O	FT	PC8	TIM3_CH3/LCD_SEG26	-
99	D12	66	40	F4	PC9	I/O	FT	PC9	TIM3_CH4/LCD_SEG27	-
100	D11	67	41	F3	PA8	I/O	FT	PA8	USART1_CK/MCO/ LCD_COM0	-
101	D10	68	42	F1	PA9	I/O	FT	PA9	USART1_TX / LCD_COM1	-

Table 9. Alternate function input/output (continued)

Port name	Digital alternate function number														
	AFIO0	AFIO1	AFIO2	AFIO3	AFIO4	AFIO5	AFIO6	AFIO7	AFIO8	. .	AFIO11	. .	AFIO14	AFIO15
	Alternate function													
	SYSTEM	TIM2	TIM3/4/5	TIM9/10/11	I2C1/2	SPI1/2	SPI3	USART1/2/3	UART4/5	-	LCD	-	CPRI	SYSTEM
PF0	-	-	-	-	-	-	-	-	-	-	-	-	-	EVENT OUT
PF1	-	-	-	-	-	-	-	-	-	-	-	-	-	EVENT OUT
PF2	-	-	-	-	-	-	-	-	-	-	-	-	-	EVENT OUT
PF3	-	-	-	-	-	-	-	-	-	-	-	-	-	EVENT OUT
PF4	-	-	-	-	-	-	-	-	-	-	-	-	-	EVENT OUT
PF5	-	-	-	-	-	-	-	-	-	-	-	-	-	EVENT OUT
PF6	-	-	TIM5_ETR	-	-	-	-	-	-	-	-	-	-	EVENT OUT
PF7	-	-	TIM5_CH2	-	-	-	-	-	-	-	-	-	-	EVENT OUT
PF8	-	-	TIM5_CH3	-	-	-	-	-	-	-	-	-	-	EVENT OUT
PF9	-	-	TIM5_CH4	-	-	-	-	-	-	-	-	-	-	EVENT OUT
PF10	-	-	-	-	-	-	-	-	-	-	-	-	-	EVENT OUT
PF11	-	-	-	-	-	-	-	-	-	-	-	-	-	EVENT OUT
PF12	-	-	-	-	-	-	-	-	-	-	-	-	-	EVENT OUT
PF13	-	-	-	-	-	-	-	-	-	-	-	-	-	EVENT OUT

5 Memory mapping

Figure 8. Memory map

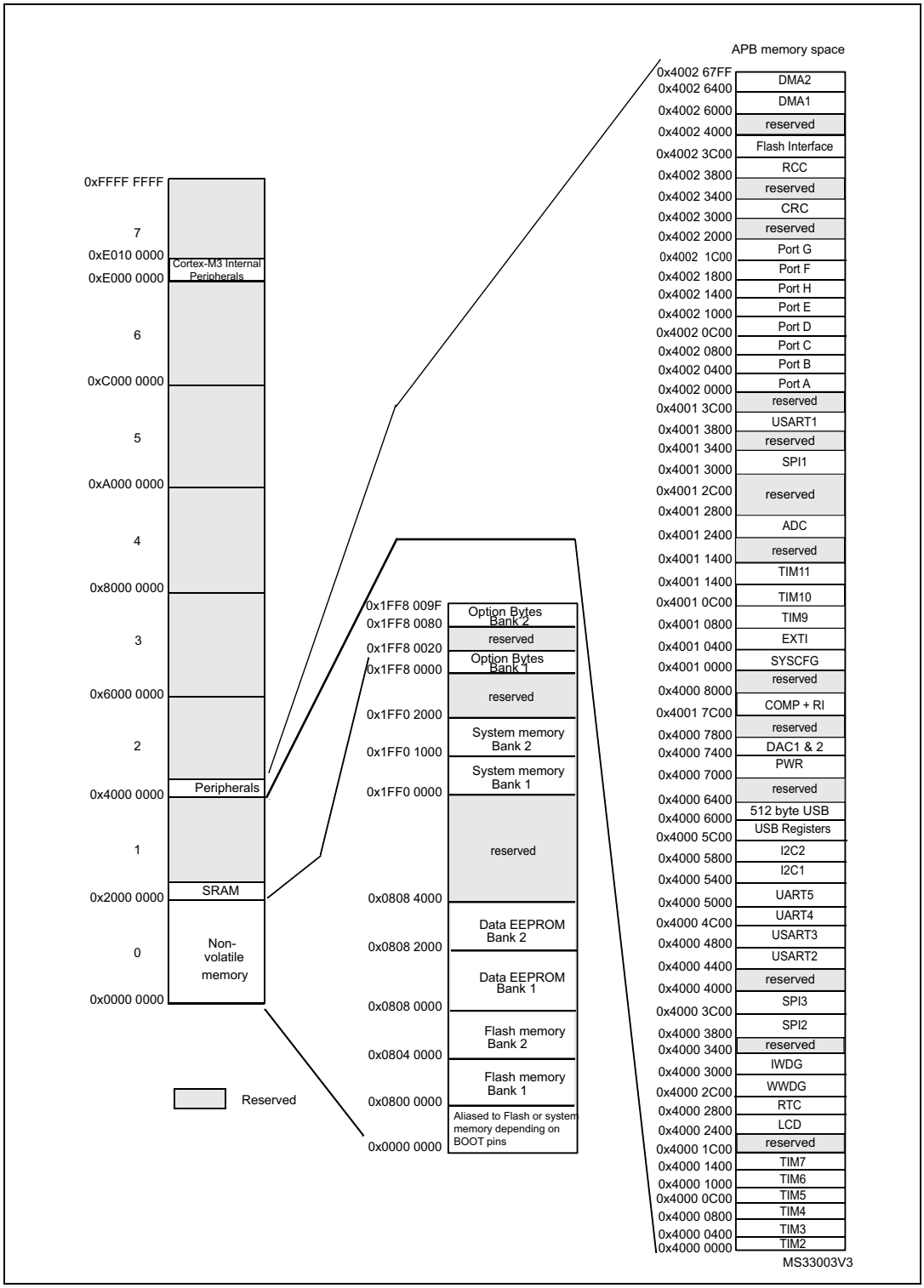


Table 14. Embedded reset and power control block characteristics (continued)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{BOR3}	Brown-out reset threshold 3	Falling edge	2.45	2.55	2.6	V
		Rising edge	2.54	2.66	2.7	
V_{BOR4}	Brown-out reset threshold 4	Falling edge	2.68	2.8	2.85	
		Rising edge	2.78	2.9	2.95	
V_{PVD0}	Programmable voltage detector threshold 0	Falling edge	1.8	1.85	1.88	
		Rising edge	1.88	1.94	1.99	
V_{PVD1}	PVD threshold 1	Falling edge	1.98	2.04	2.09	
		Rising edge	2.08	2.14	2.18	
V_{PVD2}	PVD threshold 2	Falling edge	2.20	2.24	2.28	
		Rising edge	2.28	2.34	2.38	
V_{PVD3}	PVD threshold 3	Falling edge	2.39	2.44	2.48	
		Rising edge	2.47	2.54	2.58	
V_{PVD4}	PVD threshold 4	Falling edge	2.57	2.64	2.69	
		Rising edge	2.68	2.74	2.79	
V_{PVD5}	PVD threshold 5	Falling edge	2.77	2.83	2.88	
		Rising edge	2.87	2.94	2.99	
V_{PVD6}	PVD threshold 6	Falling edge	2.97	3.05	3.09	
		Rising edge	3.08	3.15	3.20	
V_{hyst}	Hysteresis voltage	BOR0 threshold	-	40	-	mV
		All BOR and PVD thresholds excepting BOR0	-	100	-	

1. Guaranteed by characterization results.
2. Valid for device version without BOR at power up. Please see option “D” in Ordering information scheme for more details.

6.3.3 Embedded internal reference voltage

The parameters given in *Table 16* are based on characterization results, unless otherwise specified.

Table 15. Embedded internal reference voltage calibration values

Calibration value name	Description	Memory address
VREFINT_CAL	Raw data acquired at temperature of 30 °C ±5 °C V_{DDA}= 3 V ±10 mV	0x1FF8 00F8 - 0x1FF8 00F9

Table 16. Embedded internal reference voltage

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{REFINT\ out}$ (1)	Internal reference voltage	– 40 °C < T_J < +110 °C	1.202	1.224	1.242	V
I_{REFINT}	Internal reference current consumption	-	-	1.4	2.3	µA
$T_{VREFINT}$	Internal reference startup time	-	-	2	3	ms
V_{VREF_MEAS}	V_{DDA} and V_{REF+} voltage during V_{REFINT} factory measure	-	2.99	3	3.01	V
A_{VREF_MEAS}	Accuracy of factory-measured V_{REF} value(2)	Including uncertainties due to ADC and V_{DDA}/V_{REF+} values	-	-	±5	mV
T_{Coeff}(3)	Temperature coefficient	–40 °C < T_J < +110 °C	-	25	100	ppm/°C
A_{Coeff}(3)	Long-term stability	1000 hours, T= 25 °C	-	-	1000	ppm
$V_{DDCoeff}$(3)	Voltage coefficient	3.0 V < V_{DDA} < 3.6 V	-	-	2000	ppm/V
$T_{S\_vrefint}$(3)	ADC sampling time when reading the internal reference voltage	-	4	-	-	µs
T_{ADC_BUF}(3)	Startup time of reference voltage buffer for ADC	-	-	-	10	µs
I_{BUF_ADC}(3)	Consumption of reference voltage buffer for ADC	-	-	13.5	25	µA
I_{VREF_OUT}(3)	VREF_OUT output current (4)	-	-	-	1	µA
C_{VREF_OUT}(3)	VREF_OUT output load	-	-	-	50	pF
I_{LPBUF}(3)	Consumption of reference voltage buffer for VREF_OUT and COMP	-	-	730	1200	nA
V_{REFINT_DIV1}(3)	1/4 reference voltage	-	24	25	26	% V_{REFINT}
V_{REFINT_DIV2}(3)	1/2 reference voltage	-	49	50	51	
V_{REFINT_DIV3}(3)	3/4 reference voltage	-	74	75	76	

1. Guaranteed by test in production.
2. The internal V_{REF} value is individually measured in production and stored in dedicated EEPROM bytes.
3. Guaranteed by characterization results.
4. To guarantee less than 1% VREF_OUT deviation.

6.3.4 Supply current characteristics

The current consumption is a function of several parameters and factors such as the operating voltage, temperature, I/O pin loading, device software configuration, operating frequencies, I/O pin switching rate, program location in memory and executed binary code. The current consumption is measured as described in *Figure 13: Current consumption measurement scheme*.

All Run-mode current consumption measurements given in this section are performed with a reduced code that gives a consumption equivalent to the Dhrystone 2.1 code, unless otherwise specified. The current consumption values are derived from tests performed under ambient temperature T_A = 25 °C and V_{DD} supply voltage conditions summarized in *Table 13: General operating conditions*, unless otherwise specified.

The MCU is placed under the following conditions:

- All I/O pins are configured in analog input mode
- All peripherals are disabled except when explicitly mentioned.
- The Flash memory access time, 64-bit access and prefetch is adjusted depending on f_{HCLK} frequency and voltage range to provide the best CPU performance.
- When the peripherals are enabled $f_{APB1} = f_{APB2} = f_{AHB}$.
- When PLL is ON, the PLL inputs are equal to HSI = 16 MHz (if internal clock is used) or HSE = 16 MHz (if HSE bypass mode is used).
- The HSE user clock applied to OSCI_IN input follows the characteristic specified in *Table 26: High-speed external user clock characteristics*.
- For maximum current consumption $V_{DD} = V_{DDA}$ = 3.6 V is applied to all supply pins.
- For typical current consumption $V_{DD} = V_{DDA}$ = 3.0 V is applied to all supply pins if not specified otherwise.

Table 17. Current consumption in Run mode, code with data processing running from Flash

Symbol	Parameter	Conditions		f_{HCLK}	Typ	Max(1)	Unit
I_{DD} (Run from Flash)	Supply current in Run mode, code executed from Flash	$f_{HSE} = f_{HCLK}$ up to 16 MHz included, $f_{HSE} = f_{HCLK}/2$ above 16 MHz (PLL ON)(2)	Range 3, V_{CORE}=1.2 V VOS[1:0] = 11	1 MHz	225	500	µA
				2 MHz	420	750	
				4 MHz	780	1200	
			Range 2, V_{CORE}=1.5 V VOS[1:0] = 10	4 MHz	0.98	1.6	mA
				8 MHz	1.85	2.9	
				16 MHz	3.6	5.2	
			Range 1, V_{CORE}=1.8 V VOS[1:0] = 01	8 MHz	2.2	3.5	
				16 MHz	4.4	6.5	
				32 MHz	8.6	12	
		HSI clock source (16 MHz)	Range 2, V_{CORE}=1.5 V VOS[1:0] = 10	16 MHz	3.6	5.2	
			Range 1, V_{CORE}=1.8 V VOS[1:0] = 01	32 MHz	8.7	12.3	
		MSI clock, 65 kHz	Range 3, V_{CORE}=1.2 V VOS[1:0] = 11	65 kHz	42	145	µA
		MSI clock, 524 kHz		524 kHz	135	250	
		MSI clock, 4.2 MHz		4.2 MHz	820	1200	

1. Guaranteed by characterization results, unless otherwise specified.
2. Oscillator bypassed (HSEBYP = 1 in RCC_CR register).

Table 19. Current consumption in Sleep mode

Symbol	Parameter	Conditions		f_{HCLK}	Typ	Max(1)	Unit
I_{DD} (Sleep)	Supply current in Sleep mode, Flash OFF	f_{HSE} = f_{HCLK} up to 16 MHz included, f_{HSE} = f_{HCLK}/2 above 16 MHz (PLL ON)(2)	Range 3, V_{CORE}=1.2 V VOS[1:0] = 11	1 MHz	51	220	µA
				2 MHz	81	300	
				4 MHz	140	380	
			Range 2, V_{CORE}=1.5 V VOS[1:0] = 10	4 MHz	175	500	
				8 MHz	330	700	
				16 MHz	625	1100	
			Range 1, V_{CORE}=1.8 V VOS[1:0] = 01	8 MHz	395	800	
				16 MHz	760	1250	
				32 MHz	1700	2700	
		HSI clock source (16 MHz)	Range 2, V_{CORE}=1.5 V VOS[1:0] = 10	16 MHz	670	1100	
			Range 1, V_{CORE}=1.8 V VOS[1:0] = 01	32 MHz	1750	2700	
		MSI clock, 65 kHz	Range 3, V_{CORE}=1.2 V VOS[1:0] = 11	65 kHz	19	92	
		MSI clock, 524 kHz		524 kHz	33	110	
		MSI clock, 4.2 MHz		4.2 MHz	150	273	
	Supply current in Sleep mode, Flash ON	f_{HSE} = f_{HCLK} up to 16 MHz included, f_{HSE} = f_{HCLK}/2 above 16 MHz (PLL ON)(2)	Range 3, V_{CORE}=1.2 V VOS[1:0] = 11	1 MHz	63	250	
				2 MHz	93	300	
				4 MHz	155	380	
			Range 2, V_{CORE}=1.5 V VOS[1:0] = 10	4 MHz	190	500	
				8 MHz	340	700	
				16 MHz	640	1120	
			Range 1, V_{CORE}=1.8 V VOS[1:0] = 01	8 MHz	410	800	
				16 MHz	770	1300	
				32 MHz	1750	2700	
		HSI clock source (16 MHz)	Range 2, V_{CORE}=1.5 V VOS[1:0] = 10	16 MHz	690	1160	
			Range 1, V_{CORE}=1.8 V VOS[1:0] = 01	32 MHz	1750	2800	
	Supply current in Sleep mode, Flash ON	MSI clock, 65 kHz	Range 3, V_{CORE}=1.2V VOS[1:0] = 11	65 kHz	31	105	
		MSI clock, 524 kHz		524 kHz	45	125	
		MSI clock, 4.2 MHz		4.2 MHz	160	290	

1. Guaranteed by characterization results, unless otherwise specified.
2. Oscillator bypassed (HSEBYP = 1 in RCC_CR register)

Table 21. Current consumption in Low-power sleep mode

Symbol	Parameter	Conditions			Typ	Max(1)	Unit
I_{DD} (LP Sleep)	Supply current in Low-power sleep mode	All peripherals OFF, V_{DD} from 1.65 V to 3.6 V	MSI clock, 65 kHz f_{HCLK} = 32 kHz Flash OFF	T_A = -40 °C to 25 °C	5.5	-	µA
			MSI clock, 65 kHz f_{HCLK} = 32 kHz Flash ON	T_A = -40 °C to 25 °C	18.5	21	
				T_A = 85 °C	26.8	29	
				T_A = 105 °C	37	47	
			MSI clock, 65 kHz f_{HCLK} = 65 kHz, Flash ON	T_A = -40 °C to 25 °C	18.5	21	
				T_A = 85 °C	27.2	29	
				T_A = 105 °C	37.3	47	
			MSI clock, 131 kHz f_{HCLK} = 131 kHz, Flash ON	T_A = -40 °C to 25 °C	21.5	25	
				T_A = 55 °C	23.7	26	
				T_A = 85 °C	29.8	32	
				T_A = 105 °C	39.7	50	
		TIM9 and USART1 enabled, Flash ON, V_{DD} from 1.65 V to 3.6 V	MSI clock, 65 kHz f_{HCLK} = 32 kHz	T_A = -40 °C to 25 °C	18.5	21	
				T_A = 85 °C	26.8	29	
				T_A = 105 °C	38.3	47	
			MSI clock, 65 kHz f_{HCLK} = 65 kHz	T_A = -40 °C to 25 °C	18.5	21	
				T_A = 85 °C	27.2	29	
				T_A = 105 °C	38.5	47	
			MSI clock, 131 kHz f_{HCLK} = 131 kHz	T_A = -40 °C to 25 °C	21.5	25	
				T_A = 55 °C	23.7	26	
				T_A = 85 °C	29.8	32	
				T_A = 105 °C	41.2	50	
I_{DD} max (LP Sleep)	Max allowed current in Low-power sleep mode	V_{DD} from 1.65 V to 3.6 V	-	-	-	200	

1. Guaranteed by characterization results, unless otherwise specified.

Table 32. MSI oscillator characteristics (continued)

Symbol	Parameter	Condition	Typ	Max	Unit
$t_{STAB(MSI)}$ (2)	MSI oscillator stabilization time	MSI range 0	-	40	µs
		MSI range 1	-	20	
		MSI range 2	-	10	
		MSI range 3	-	4	
		MSI range 4	-	2.5	
		MSI range 5	-	2	
		MSI range 6, Voltage range 1 and 2	-	2	
		MSI range 3, Voltage range 3	-	3	
$f_{OVER(MSI)}$	MSI oscillator frequency overshoot	Any range to range 5	-	4	MHz
		Any range to range 6	-	6	

1. This is a deviation for an individual part, once the initial frequency has been measured.
2. Guaranteed by characterization results.

Table 52. USB: full speed electrical characteristics (continued)

Driver characteristics[1]					
Symbol	**Parameter**	**Conditions**	**Min**	**Max**	**Unit**
t_{rfm}	Rise/ fall time matching	t_r/t_f	90	110	%
V_{CRS}	Output signal crossover voltage		1.3	2.0	V

1. Guaranteed by design.
2. Measured from 10% to 90% of the data signal. For more detailed informations, please refer to USB Specification - Chapter 7 (version 2.0).

I2S characteristics

Table 53. I2S characteristics

Symbol	Parameter	Conditions	Min	Max	Unit
f_{MCK}	I2S Main Clock Output		256 x 8K	256xFs (1)	MHz
f_{CK}	I2S clock frequency	Master data: 32 bits	-	64xFs	MHz
		Slave data: 32 bits	-	64xFs	
D_{CK}	I2S clock frequency duty cycle	Slave receiver, 48KHz	30	70	%
$t_{r(CK)}$	I2S clock rise time	Capacitive load CL=30pF	-	8	ns
$t_{f(CK)}$	I2S clock fall time			8	
$t_{v(WS)}$	WS valid time	Master mode	4	24	
$t_{h(WS)}$	WS hold time	Master mode	0	-	
$t_{su(WS)}$	WS setup time	Slave mode	15	-	
$t_{h(WS)}$	WS hold time	Slave mode	0	-	
$t_{su(SD\_MR)}$	Data input setup time	Master receiver	8	-	
$t_{su(SD\_SR)}$	Data input setup time	Slave receiver	9	-	
$t_{h(SD\_MR)}$	Data input hold time	Master receiver	5	-	
$t_{h(SD\_SR)}$		Slave receiver	4	-	
$t_{v(SD\_ST)}$	Data output valid time	Slave transmitter (after enable edge)	-	64	
$t_{h(SD\_ST)}$	Data output hold time	Slave transmitter (after enable edge)	22	-	
$t_{v(SD\_MT)}$	Data output valid time	Master transmitter (after enable edge)	-	12	
$t_{h(SD\_MT)}$	Data output hold time	Master transmitter (after enable edge)	8	-	

1. The maximum for 256xFs is 8 MHz

Note: Refer to the I2S section of the product reference manual for more details about the sampling frequency (Fs), f_{MCK}, f_{CK} and D_{CK} values. These values reflect only the digital peripheral behavior, source clock precision might slightly change them. DCK depends mainly on the

6.3.20 Temperature sensor characteristics

Table 60. Temperature sensor calibration values

Calibration value name	Description	Memory address
TS_CAL1	TS ADC raw data acquired at temperature of 30 °C ±5 °C V_{DDA}= 3 V ±10 mV	0x1FF8 00FA - 0x1FF8 00FB
TS_CAL2	TS ADC raw data acquired at temperature of 110 °C ±5 °C V_{DDA}= 3 V ±10 mV	0x1FF8 00FE - 0x1FF8 00FF

Table 61. Temperature sensor characteristics

Symbol	Parameter	Min	Typ	Max	Unit
T_L(1)	V_{SENSE} linearity with temperature	-	±1	±2	°C
Avg_Slope(1)	Average slope	1.48	1.61	1.75	mV/°C
V_{110}	Voltage at 110°C ±5°C(2)	612	626.8	641.5	mV
$I_{DDA(TEMP)}$(3)	Current consumption	-	3.4	6	µA
t_{START}(3)	Startup time	-	-	10	µs
T_{S_temp}(3)	ADC sampling time when reading the temperature	4	-	-	

1. Guaranteed by characterization results.
2. Measured at V_{DD} = 3 V ±10 mV. V110 ADC conversion result is stored in the TS_CAL2 byte.
3. Guaranteed by design.

6.3.21 Comparator

Table 62. Comparator 1 characteristics

Symbol	Parameter	Conditions	Min(1)	Typ	Max(1)	Unit
V_{DDA}	Analog supply voltage	-	1.65		3.6	V
R_{400K}	R_{400K} value	-	-	400	-	kΩ
R_{10K}	R_{10K} value	-	-	10	-	
V_{IN}	Comparator 1 input voltage range	-	0.6	-	V_{DDA}	V
t_{START}	Comparator startup time	-	-	7	10	µs
td	Propagation delay(2)	-	-	3	10	
Voffset	Comparator offset	-	-	±3	±10	mV
$d_{Voffset}$/dt	Comparator offset variation in worst voltage stress conditions	V_{DDA} = 3.6 V V_{IN+} = 0 V V_{IN-} = V_{REFINT} T_A = 25 °C	0	1.5	10	mV/1000 h
I_{COMP1}	Current consumption(3)	-	-	160	260	nA

6.3.22 LCD controller

The device embeds a built-in step-up converter to provide a constant LCD reference voltage independently from the V_{DD} voltage. An external capacitor C_{ext} must be connected to the V_{LCD} pin to decouple this converter.

Table 64. LCD controller characteristics

Symbol	Parameter	Min	Typ	Max	Unit
V_{LCD}	LCD external voltage	-	-	3.6	V
V_{LCD0}	LCD internal reference voltage 0	-	2.6	-	
V_{LCD1}	LCD internal reference voltage 1	-	2.73	-	
V_{LCD2}	LCD internal reference voltage 2	-	2.86	-	
V_{LCD3}	LCD internal reference voltage 3	-	2.98	-	
V_{LCD4}	LCD internal reference voltage 4	-	3.12	-	
V_{LCD5}	LCD internal reference voltage 5	-	3.26	-	
V_{LCD6}	LCD internal reference voltage 6	-	3.4	-	
V_{LCD7}	LCD internal reference voltage 7	-	3.55	-	
C_{ext}	V_{LCD} external capacitance	0.1	-	2	µF
I_{LCD}(1)	Supply current at V_{DD} = 2.2 V	-	3.3	-	µA
	Supply current at V_{DD} = 3.0 V	-	3.1	-	
R_{Htot}(2)	Low drive resistive network overall value	5.28	6.6	7.92	MΩ
R_L(2)	High drive resistive network total value	192	240	288	kΩ
V_{44}	Segment/Common highest level voltage	-	-	V_{LCD}	V
V_{34}	Segment/Common 3/4 level voltage	-	3/4 V_{LCD}	-	V
V_{23}	Segment/Common 2/3 level voltage	-	2/3 V_{LCD}	-	
V_{12}	Segment/Common 1/2 level voltage	-	1/2 V_{LCD}	-	
V_{13}	Segment/Common 1/3 level voltage	-	1/3 V_{LCD}	-	
V_{14}	Segment/Common 1/4 level voltage	-	1/4 V_{LCD}	-	
V_0	Segment/Common lowest level voltage	0	-	-	
ΔVxx(3)	Segment/Common level voltage error T_A = -40 to 105 °C	-	-	±50	mV

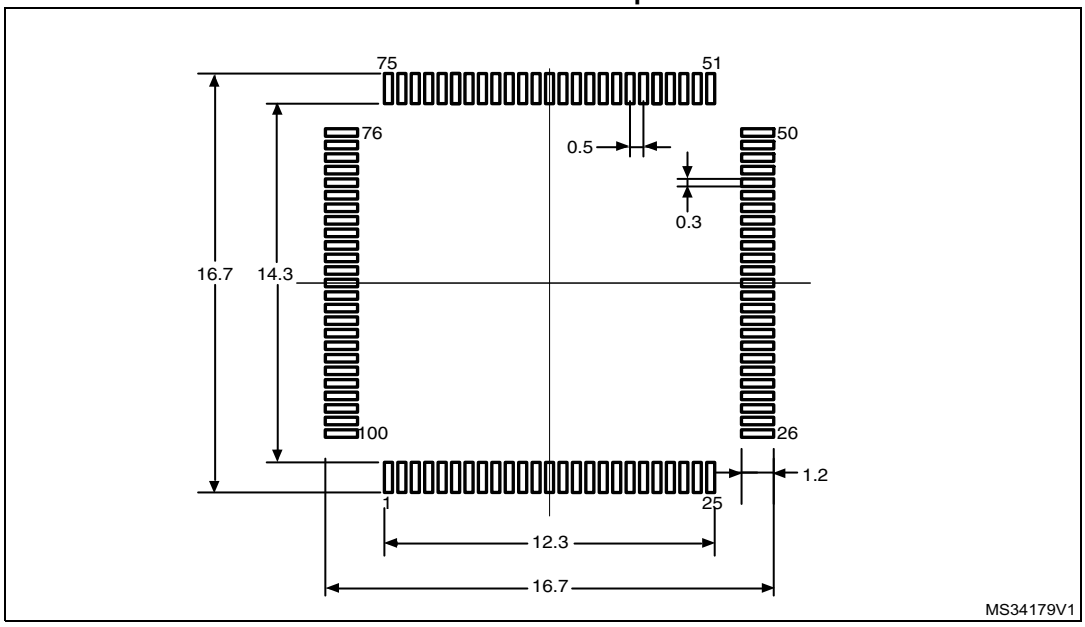
1. LCD enabled with 3 V internal step-up active, 1/8 duty, 1/4 bias, division ratio= 64, all pixels active, no LCD connected.
2. Guaranteed by design.
3. Guaranteed by characterization results.

Table 66. LQPF100, 14 x 14 mm, 100-pin low-profile quad flat package mechanical data (continued)

Symbol	millimeters			inches[1]		
	Min	Typ	Max	Min	Typ	Max
E3	-	12.000	-	-	0.4724	-
e	-	0.500	-	-	0.0197	-
L	0.450	0.600	0.750	0.0177	0.0236	0.0295
L1	-	1.000	-	-	0.0394	-
k	0.0°	3.5°	7.0°	0.0°	3.5°	7.0°
ccc	-	-	0.080	-	-	0.0031

1. Values in inches are converted from mm and rounded to 4 decimal digits.

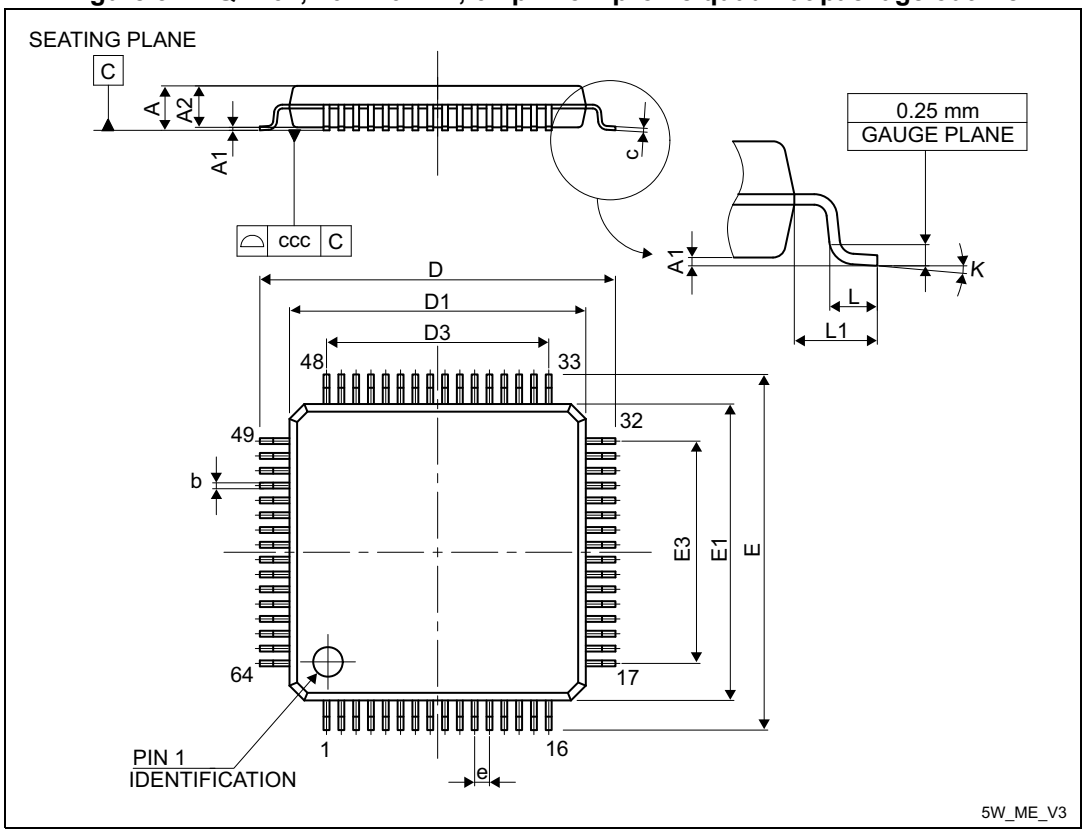
Figure 35. LQFP100, 14 x 14 mm, 100-pin low-profile quad flat package recommended footprint



1. Dimensions are in millimeters.

7.3 LQFP64, 10 x 10 mm, 64-pin low-profile quad flat package information

Figure 37. LQFP64, 10 x 10 mm, 64-pin low-profile quad flat package outline



1. Drawing is not to scale.

Table 67. LQFP64, 10 x 10 mm 64-pin low-profile quad flat package mechanical data

Symbol	millimeters			inches[1]		
	Min	Typ	Max	Min	Typ	Max
A	-	-	1.600	-	-	0.0630
A1	0.050	-	0.150	0.0020	-	0.0059
A2	1.350	1.400	1.450	0.0531	0.0551	0.0571
b	0.170	0.220	0.270	0.0067	0.0087	0.0106
c	0.090	-	0.200	0.0035	-	0.0079
D	-	12.000	-	-	0.4724	-
D1	-	10.000	-	-	0.3937	-
D3	-	7.500	-	-	0.2953	-
E	-	12.000	-	-	0.4724	-
E1	-	10.000	-	-	0.3937	-

Table 73. Document revision history (continued)

Date	Revision	Changes
10-Feb-2015	6	Updated *Section : In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.* with new package device marking. Updated *Figure 8: Memory map*.
27-Apr-2015	7	Updated *Section 7: Package information* structure: Paragraph titles and paragraph heading level. Updated *Section 7.1: LQFP144, 20 x 20 mm, 144-pin low-profile quad flat package information* removing gate mark in *Figure 33* and adding text for device orientation versus pin1 identifier. Updated *Section 7.2: LQFP100, 14 x 14 mm, 100-pin low-profile quad flat package information* removing gate mark in *Figure 36* and adding note for device orientation versus pin 1 identifier. Updated *Section 7: Package information* for all other package device marking adding text in for device orientation versus pin 1 or ball A1 identifier. Added *Figure 44: WLCSP104, 0.4 mm pitch wafer level chip scale package recommended footprint* and *Table 70: WLCSP104, 0.4 mm pitch recommended PCB design rules*. Updated *Table 8: STM32L151xE and STM32L152xE pin definitions* ADC inputs. Updated *Table 16: Embedded internal reference voltage* temperature coefficient at 100ppm/°C. and table footnote 3: “guaranteed by design” changed by “guaranteed by characterization results”. Updated *Table 63: Comparator 2 characteristics* new maximum threshold voltage temperature coefficient at 100ppm/°C.
09-Feb-2016	8	Updated cover page putting eight SPIs in the peripheral communication interface list. Updated *Table 2: Ultra-low-power STM32L151xE and STM32L152xE device features and peripheral counts* SPI and I2S lines. Updated *Table 39: ESD absolute maximum ratings* CDM class II by class C3 and C4 depending of the package. Updated all the notes, removing ‘not tested in production’. Updated *Table 10: Voltage characteristics* adding note about V_{REF-} pin. Updated *Table 5: Functionalities depending on the working mode (from Run/active down to standby)* LSI and LSE functionalities putting “Y” in Standby mode.